

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

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Listing of Claims:

Claim 1 (currently amended) A method of manufacturing a reflector comprising:

- 10 providing a substrate;
simultaneously forming at least one thin film transistor and a plurality of bumpy stacked structures on the substrate, each of the bumpy stacked structures comprising a plurality of sub-stacked layers which have at least two different widths;
15 ~~forming a plurality of stacked structures on the substrate, each of the stacked structures comprising a plurality of sub-stacked layers, which have at least two different kinds of widths;~~
forming a thin film layer for covering the thin film transistor and the plurality of bumpy stacked structures;
20 forming a contact hole in the thin film layer; and
depositing a reflective metal layer on the thin film layer;
wherein the reflective metal layer is electrically connected to the thin film transistor through the contact hole.

25 Claims 2-3 (cancelled)

Claim 4 (original) The method of claim 1 wherein the thin film layer is a laminated layer comprising a photoresist layer, an organic layer, and an inorganic passivation layer.

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Claim 5 (currently amended) The method of claim 4 wherein a method of forming the contact hole comprises:

forming the inorganic passivation layer on the thin film transistor
and the plurality of bumpy stacked structures;
forming the organic layer on the inorganic passivation layer;
forming the photoresist layer on the organic layer;
5 performing a photolithography process for forming a predetermined
pattern in the photoresist layer;
etching the organic layer and the inorganic passivation layer along
the predetermined pattern so as to form the contact hole;
removing the photoresist layer; and
10 performing a baking process for smoothening the organic layer.

Claim 6 (original) The method of claim 1 wherein the thin film layer is a
laminated layer comprising an organic layer and an inorganic
passivation layer, and the organic layer is made of a photoresist
15 material.

Claim 7 (currently amended) The method of claim 6 wherein a method of
forming the contact hole comprises:
forming the inorganic passivation layer on the thin film transistor
20 and the plurality of bumpy stacked structures;
forming the organic layer on the inorganic passivation layer;
performing a photolithography process for forming a predetermined
pattern in the organic layer;
etching the inorganic passivation layer along the predetermined
25 pattern so as to form the contact hole; and
performing a baking process for smoothening the organic layer.

Claim 8 (original) The method of claim 1 wherein the thin film layer is
an organic passivation layer, which is made of a photoresist material.
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Claim 9 (currently amended) The method of claim 8 wherein a method of
forming the contact hole comprises:

forming the organic passivation layer on the thin film transistor and the plurality of bumpy stacked structures;
performing an exposing process for forming a predetermined pattern in the organic passivation layer;
5 performing a developing process on the organic passivation layer so as to form the contact hole; and
performing a baking process for smoothening the organic passivation layer.

10 Claim 10 (original) The method of claim 1 wherein each of the sub-stacked layers is formed from a material selected from the group consisting of an insulating layer, a gate electrode layer, an amorphous silicon layer, an N⁺ silicon layer, and a metal layer.

15 Claim 11 (original) The method of claim 1 wherein each of the sub-stacked layers is formed from a material selected from the group consisting of a gate electrode, a common electrode, an insulating layer, an amorphous silicon layer, an N⁺ silicon layer, a metal layer, a source electrode, a drain electrode, and a passivation layer.

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